

IN THE SPECIFICATION:

Please replace paragraph number [0001] with the following rewritten paragraph:

[0001] This application is a continuation of application Serial No. 10/011,134, filed December 7, 2001, ~~pending now~~ U.S. Patent 6,653,234, issued November 25, 2003, which is a continuation of application Serial No. 09/730,038, filed December 5, 2000, now U.S. Patent 6,340,637, issued January 22, 2002, which is a continuation of application Serial No. 09/292,993, filed April 16, 1999, now U.S. Patent 6,184,136, issued February 6, 2001, which is a continuation of application Serial No. 08/581,765, filed January 2, 1996, now U.S. Patent 5,946,594, issued August 31, 1999.

Please replace paragraph number [0012] with the following rewritten paragraph:

[0012] Still referring to FIG. 1, the premixed gas combination of TiCl₄ and the hydrocarbon gas enters deposition chamber 4 through shower head 15. A radio-frequency voltage, supplied by radio-frequency generator 8, is applied between substrate holder 6 and deposition chamber 4, thus forming alkyl radicals from the hydrocarbon gas in the space above the semiconductor wafer 5. The TiCl₄ is adsorbed on the surface of the semiconductor wafer 5, and alkyl radicals react with the adsorbed TiCl₄ molecules to deposit a uniformly thick titanium metal layer on all exposed surfaces of the semiconductor wafer. As high temperatures favor the formation of inorganic halides as opposed to titanium metal, the reaction temperature is maintained within a range of about 200° C. to 500° C. Although the desired reaction will occur at a pressure within a range of about 2 to 100 torr, a preferred range is deemed to be about 2 to 5 torr. A constant deposition pressure within that preferred range is monitored and maintained by conventional pressure control components consisting of pressure sensor 9, pressure switch 10, air operating vacuum valve 11 and pressure control valve 12. The alkyl chloride gas given off as a byproduct of the reaction, whether methyl chloride (CH₃Cl) or an alkyl chloride, and the carrier gases (if carrier gases are used) pass through particulate filter-16 14 and escape through exhaust vent-13 16 with the aid of a Roots blower-14 13 to complete the process.